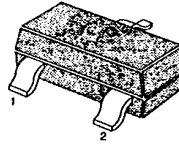


MMBT4126**PNP EPITAXIAL SILICON TRANSISTOR****GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-25	V
Collector-Emitter Voltage	V _{CE0}	-25	V
Emitter-Base Voltage	V _{EB0}	-4	V
Collector Current	I _C	-200	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C
Thermal Resistance Junction to Ambient	R _{th(j-a)}	357	°C/W

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _C = -10μA, I _E = 0	-25		V
*Collector-Emitter Breakdown Voltage	BV _{CE0}	I _C = -1mA, I _E = 0	-25		V
Emitter-Base Breakdown Voltage	BV _{EB0}	I _E = -10μA, I _C = 0	-4		V
Collector Cutoff Current	I _{CB0}	V _{CB} = -20V, I _E = 0		-50	nA
Emitter Cutoff Current	I _{EB0}	V _{BE} = -3V, I _C = 0		-50	nA
*DC Current Gain	h _{FE}	V _{CE} = -1V, I _C = -2mA	120	360	
		V _{CE} = -1V, I _C = -50mA	60		
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -50mA, I _B = -5mA		-0.4	V
*Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = -50mA, I _B = -5mA		-0.95	V
Current Gain-Bandwidth Product	f _T	V _{CE} = -20V, I _C = -10mA, f = 100MHz	250		MHz
Collector Input Capacitance	C _{ib}	V _{BE} = -0.5V, I _C = 0, f = 1MHz		10	pF
Collector-Base Capacitance	C _{cb}	V _{CB} = -5V, I _E = 0, f = 1MHz		4.5	pF
Noise Figure	NF	V _{CE} = -5V, I _C = -100μA, R _s = 1kΩ Noise Bandwidth = 10Hz to 15.7KHz		4	dB

* Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

Marking

